

Supporting Information

Dynamics of Photogenerated Charge Carriers in WO₃/BiVO₄ Heterojunction Photoanodes

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XRPD analysis

In Figure SI1A the XRPD patterns are reported for the three here investigated films; the diffraction pattern recorded with FTO alone is also shown for comparison. The patterns of both individual materials fit well with monoclinic structures (JCPDS 05-0363 for WO_3 and JCPDS 75-1867 for BiVO_4). WO_3 patterns didn't match completely in the 23-25 degrees 2θ region, where the three closely spaced peaks typical of the monoclinic structures overlap. Peak broadening could be probably attributed to non-constructive scattering due to the small crystallite size of the WO_3 film.^{1,2} The combined $\text{WO}_3/\text{BiVO}_4$ electrode shows peaks of both monoclinic materials. The BiVO_4 peak at 18.6 degrees was much lower in magnitude with respect to those of single material films (a magnification of the four XRPD patterns in the 17-37 degrees 2θ region is reported in Figure SI1B). A possible explanation is that the BiVO_4 layer grows with a preferential orientation on the underlying WO_3 .

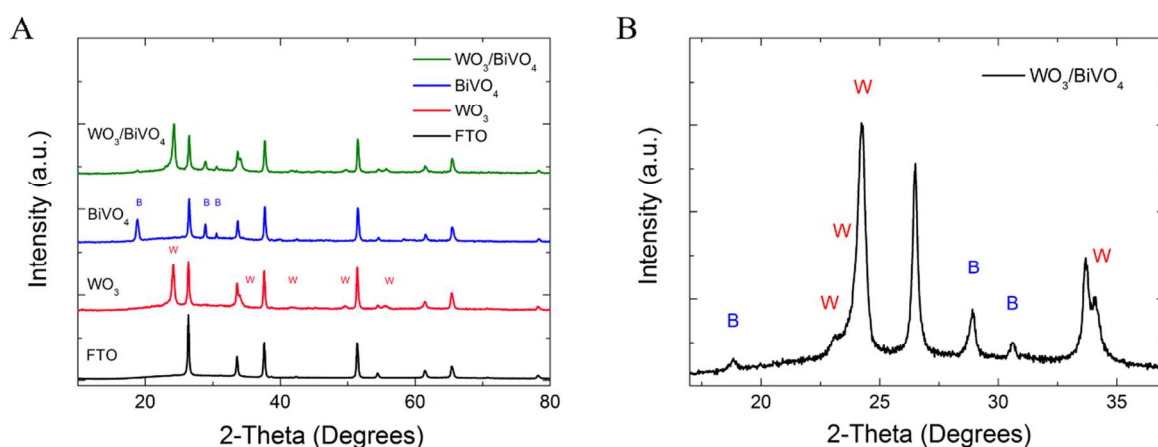


Figure SI1. (A) XRPD patterns of the materials. From the bottom: FTO glass and WO_3 , BiVO_4 and $\text{WO}_3/\text{BiVO}_4$ electrodes on FTO after 8 h annealing at 500°C . (B) Magnification of the XRPD patterns of the composite $\text{WO}_3/\text{BiVO}_4$ material, exhibiting patterns of both WO_3 and BiVO_4 , labelled as W and B, respectively.

Estimation of the band gap position of WO_3 , BiVO_4 and $\text{WO}_3/\text{BiVO}_4$ electrodes

In order to confirm the band gap position of the materials, PEC experiments were carried out with the films in contact with a Na_2SO_3 solution. This electron donor quickly fills surface holes, thus minimizing electron-hole recombination. By this way the photocurrent onset is shifted to negative potentials

providing a good approximation of the flat band potential. PEC measurements are reported in Figure S12, with the insets showing magnified views of the photocurrent profiles near the onset potential.

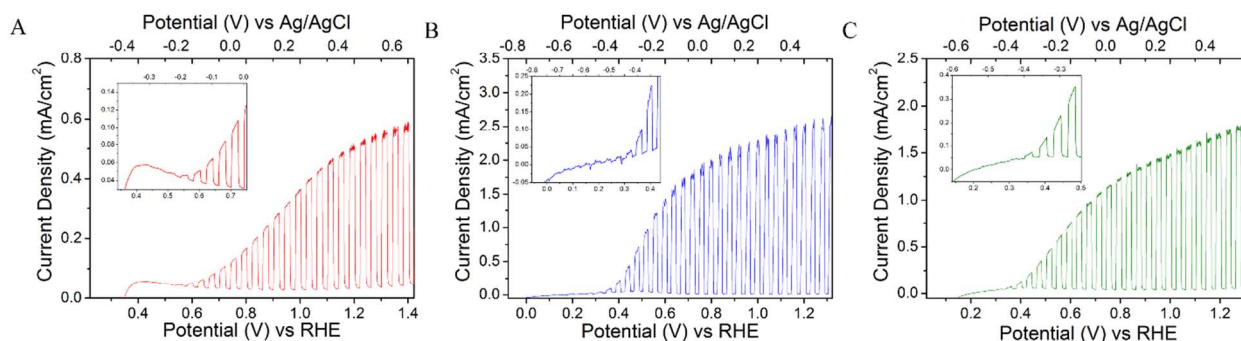
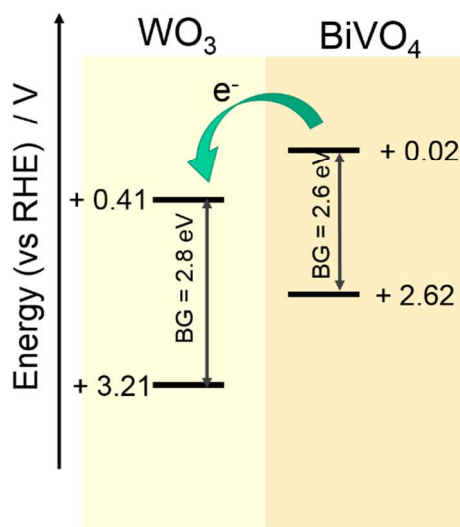


Figure S12. Current density vs applied potential experiments in the presence of Na₂SO₃ (electron donor) measured with A) the WO₃, B) the BiVO₄ and C) the WO₃/BiVO₄ electrode. The insets show magnifications close to the onset potential.

The conduction band edge positions of WO₃ and BiVO₄ are +0.41 V and +0.02 V, respectively (Scheme S11), in agreement with those reported in the literature.³ When compared to the flat band potential of BiVO₄, that of the composite material results shifted by 170 mV to positive potentials. The positive shift is consistent with a shift of the Fermi level due to electron equilibration at the interface between the two materials. The conduction bands of all investigated materials are more negative in energy than the TH reduction potential (+0.48 eV).⁴



Scheme S11. Diagram of the band edge positions of the single materials.

References

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